

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,809,362 B2
DATED : October 26, 2004
INVENTOR(S) : Terry L. Gilton

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [56], **References Cited**, OTHER PUBLICATIONS,

"Hegab, N.A.; Fadel, M.; Sedeek, K., Memory switching phenomena in thin films of chalcogenide semiconductors, Vacuum 45 (1994) 459-462." should read

-- Hegab, N.A.; Fadel, M.; Sedeek, K., Memory switching phenomena in thin films of chalcogenide semiconductors, Vacuum 45 (1994) 459-462. --;

"Neale, R.G.; Aseltine, J.A., The application of amorphous materials to computer memories, IEEE transactions on electron dev. Ed-20 (1973) 195-209." should read

-- Neale, R.G.; Aseltine, J.A., The application of amorphous materials to computer memories, IEEE transactions on electron dev. Ed-20 (1973) 195-209. --;

"Zhang, M.; Mancini, S.; Bresser, W.; Boolchang, P., Variation of glass transition temperature T_g , with average coordination number, $\langle m \rangle$, in network glasses: evidence of a threshold behavior in the slope $|dT_g/d\langle m \rangle|$ at the rigidity percolation threshold ($\langle m \rangle = 2.4$), J. Non-Cryst. Solids 151 (1992) 149-154." should read

-- Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature T_g , with average coordination number, $\langle m \rangle$, in network glasses: evidence of a threshold behavior in the slope $|dT_g/d\langle m \rangle|$ at the rigidity percolation threshold ($\langle m \rangle = 2.4$), J. Non-Cryst. Solids 151 (1992) 149-154. --.

Signed and Sealed this

Sixth Day of December, 2005



JON W. DUDAS

Director of the United States Patent and Trademark Office